



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-252 Plastic-Encapsulate Transistors

2SC4003 TRANSISTOR (NPN)

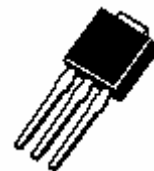
FEATURES

- High h_{FE} $h_{FE}=60$ to 200
- low $V_{CE(sat)}$ $V_{CE(sat)}=0.6V$

MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.2	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

TO-251
TO-252-2L



1. BASE

2. COLLECTOR



3. EMITTER

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=300V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=10V, I_C=50mA$	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=5mA$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=5mA$			1	V
Transition frequency	f_T	$V_{CE}=30V, I_C=10mA$		70		MHz

CLASSIFICATION OF h_{FE}

Rank	D	E
Range	60-120	100-200

Typical Characteristics

2SC4003

